

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
31 March 2005 (31.03.2005)

PCT

(10) International Publication Number
WO 2005/029599 A3

(51) International Patent Classification⁷: **H01L 33/00**

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(21) International Application Number:
PCT/JP2004/014464

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(22) International Filing Date:
24 September 2004 (24.09.2004)

(81) Designated States (*unless otherwise indicated, for every kind of national protection available*): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
2003-331060 24 September 2003 (24.09.2003) JP

(84) Designated States (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

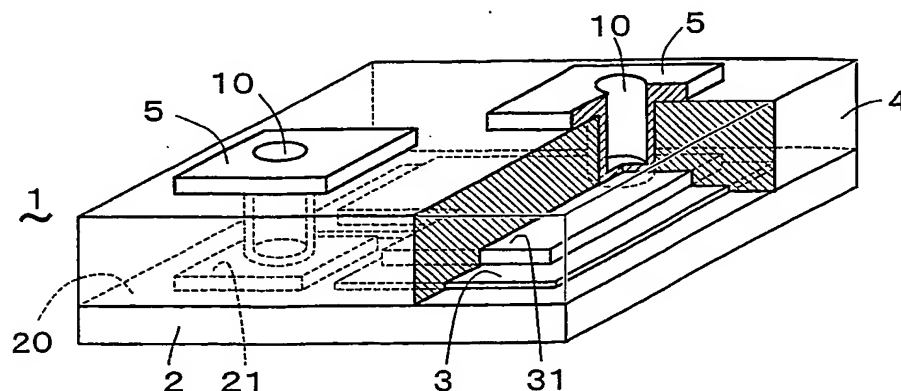
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(54) Title: SEMICONDUCTOR LIGHT-EMITTING DEVICE AND ITS MANUFACTURING METHOD



(57) Abstract: In a light-emitting device and its manufacturing method, mounting by batch process with surface-mount technology, high light extraction efficiency, and low manufacturing cost are realized. The light-emitting device 1 comprises semiconductor layers (2, 3) of p-type and n-type nitride semiconductor, semiconductor-surface-electrodes (21, 31) to apply currents into each of the semiconductor layers (2, 3), an insulating layer 4 which holds the semiconductor layers (2, 3), and mount-surface-electrodes (5). The semiconductor layers (2) has a non-deposited area 20 where the other semiconductor layer (3) is not deposited. The insulating layer (4) has VIA 10 which electrically connect the mount-surface-electrodes 5 and the semiconductor-surface-electrodes (21, 31). In the manufacturing process, firstly, semiconductor layers (2, 3) and semiconductor-surface-electrodes (21, 31) are deposited on the transparent crystal substrate, and by using build-up process, insulating layer (4) and the mount-surface-electrodes (5) are formed, and secondly, VIA 10 are formed, and finally, the transparent crystal substrate is separated to get light-emitting device (1). Light can be extracted directly and efficiently from the semiconductor layers (2, 3). With the mount-surface-electrodes (21, 31), light-emitting device (1) can be mounted by using surface mount technology.



Published:

- with international search report
- before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(88) Date of publication of the international search report:
17 November 2005